PATENT
Docket No.: 29287/137

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS	:	Satoru HANZAWA et al.	
SERIAL NO.	:	(Con. of 10/201,317)	GROUP ART UNIT: 2818
FILED	:	24 June 2003	EXAMINER: Viet D. Nguyen
FOR	:	SEMICONDUCTOR DEVICE	

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PRELIMINARY AMENDMENT

SIR:

Prior to examination of the above-identified continuation application, please enter the following amendment:

In the Specification:

Please amend the specification as follows:

Page 1: After the title, insert: This is a continuation of application number 10/201,317 filed 24 July 2002, which is a division of application number 09/706,374 filed 3 November 2000, the contents of which are incorporated herein by reference in their entirety.

Page 6: Replace the paragraph starting on line 13 with the following amended paragraph:

However, when a MOS transistor having the same ~~tox~~ oxidation film thickness (tox), as the peripheral transistors is used in sub-word drivers, the sub-word line voltage amplitude for the three values required for the capacitive coupling 2-transistor cell, as related above, is larger than the supply voltage amplitude so that the MOS transistor breakdown voltage problem is unavoidable.

Page 8: Replace the description of Fig. 16, lines 23-25, with the following amended description:

FIG. 16 ~~is~~ shows operation timing diagrams of the sub-word driver for generating the three value voltage levels of the third embodiment.

Pag 8: Replace the description of Fig. 17, lines 26-28, with the following amended description:

FIG. 17 ~~is~~ shows operation timing diagrams of the sub-word driver for generating the three value voltage levels of the third embodiment.

Page 9: Replace the description of Fig. 21, lines 8-10, with the following amended description:

FIG. 21 ~~is~~ shows operation timing diagrams of the sub-word driver for generating the three value voltage levels of the fourth embodiment.